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1
2 **SiC-TiC nanocomposite for bulk solar absorbers applications:**
3 **Effect of density and surface roughness on the optical properties**

4
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14
15 Keywords: SiC ; TiC ; Concentrated Solar Power ; selectivity ; density ; roughness

16
17 **Abstract**

18 In this study, the potential of SiC-TiC nano-composites as solar absorbers has been studied. For solar
19 thermal applications, materials with high solar absorptance and low emittance are ideally sought for
20 (spectral selectivity). A semi-molecular sol-gel synthesis route leading to nanometric homogenous
21 composites was described. The resulting SiC-TiC nanocomposite powder was sintered at different
22 temperatures to produce samples with various relative densities (from 57 to 96 %). The samples
23 morphology and composition were characterised by several techniques including Scanning Electron
24 Microscopy (SEM), Energy-Dispersive X-Ray Spectroscopy (EDX), X-Ray Diffraction (XRD),
25 carbon and oxygen elemental analyses. The link between the surface roughness and the relative
26 density was precised and the effects on the optical properties (0.25 to 25 μm wavelength range) were
27 studied. Comparisons were made with pure SiC and pure TiC samples with various relative densities.
28 Overall, the sample emittance was found to strongly decrease with the increase in the relative
29 density, leading to a great increase in the spectral selectivity, despite a little decrease in the solar
30 absorptance. The TiC-SiC composite has an intermediate reflectance compared to the pure SiC and
31 the pure TiC samples. With an absorptance of 0.76, an emittance of 0.44 and a selectivity of 1.74, the
32 denser SiC-TiC could be a good candidate for bulk solar applications.

33

34 1. Introduction

35

36 The development of a sustainable, efficient and renewable energy power is a great challenge for our
37 generation. In this context, particular attention is given to concentrating solar power (CSP) as it is a
38 promising technology to improve the efficiency of the solar-to-electricity conversion [1, 2]. In this
39 system, the absorber plays a key role by transferring the energy from solar radiation to a heat transfer
40 fluid (HTF), which will be used in a thermodynamical cycle to produce electricity. However,
41 because of thermal losses (by radiation, conduction and convection), the energy received by the
42 absorber is not completely transferred to the HTF. As the operating temperature of the absorber is
43 high (up to 1000°C), the main energy losses are due to thermal radiation. Indeed, when the absorber
44 is heated, it can behave like a blackbody and emit radiation in the infrared wavelength region
45 towards its environment. To maximize the energy efficiency, the absorber should be spectrally
46 selective: absorbing a maximum of energy in the solar spectrum wavelength region (0.25 – 2.5 μm),
47 while having a low thermal emittance in the IR region (above 2.5 μm), so that thermal re-radiation
48 losses by the heated absorber are kept low [3-6]. In addition to be spectrally selective, the material
49 constituting the absorber should be resistant to the extreme operating conditions under concentrated
50 solar irradiation (high temperatures, oxidative/corrosive atmospheres, thermal cycles, etc.).

51

52 Nowadays, one of the materials commonly used as high temperature absorber is silicon carbide,
53 because of its high oxidation resistance, its good mechanical properties and high sunlight
54 absorptance [7]. However, SiC is not spectrally selective as it has a high spectral emittance [8, 9].
55 Transition metal carbides, nitrides and borides of column IV have been subject of many
56 investigations due to their inherent spectral selectivity [10-24]. Among these materials, titanium
57 carbide could be a good candidate because it is spectrally selective and it has good mechanical
58 properties. However, it also has a low resistance to oxidation [25-32]. Previous studies showed that
59 the combination of SiC and TiC in a nanocomposite material could be a good solution to obtain a
60 material that is spectrally selective as well as resistant to oxidation [33].

61 The literature reports the combination of SiC and TiC in a composite structure to produce materials
62 with higher relative density and improved mechanical properties (fracture toughness, Vickers
63 hardness), thermal and electrical conductivity [34-44]. These properties are required for the absorber
64 material as it will endure extreme operating conditions.

65

66 Several parameters have an impact on the optical properties of the materials.

67 First, the apparent density of the material leads to changes in the optical properties of the samples.

68 The apparent density results from the process used for the material elaboration and corresponds to

69 porosity in the range of a few micrometers. Several studies indicate that the denser the material, the
70 higher the reflectance in the whole range of wavelengths. Dense materials have a little lower
71 absorptance (α) but above all a lower emittance (ϵ), thus a higher spectral selectivity which is
72 defined as the ratio α/ϵ [19, 20, 23, 45-47].

73 Second, the surface roughness increases the absorptance of radiations in the range of wavelength
74 lower than the average size of the holes and scratches (a few nanometers to a few hundred
75 nanometers) [5, 6, 20, 23, 46-50]. For example, the surface patterning of zirconium boride samples
76 by femtolaser led to better absorptance but also to higher emittance [48, 49]. The increase in the
77 absorptance and in the emittance with the surface roughness was also noticed for SiC and TiC
78 samples, in a preliminary study reported in Supplementary Information 1.

79

80 In most studies concerning the optical properties of UHTCs (Ultra-High Temperature Ceramics),
81 densified or porous samples are obtained from commercial powders. To produce composites, several
82 powders are generally mixed and sintered together. However, mechanical mixing generally induces
83 inhomogeneities and sometimes impurities in the final composite. In the conventional process, TiC
84 and SiC are usually synthesized by the carbothermal reduction of TiO_2 or SiO_2 with carbon black.
85 This reaction requires high temperature (1800 – 2200°C), long reaction time (10 – 24h) and often
86 leads to coarse-grained powders [51-53]. With nano-sized particles, the temperature (and/or time)
87 needed for carbothermal reduction would decrease [54-58]. In addition, working with nano-sized
88 materials would improve the homogeneity of the final products and lead to an intimate mixture of
89 SiC and TiC particles.

90 Molecular routes were proposed to create proximity between the metal and the carbon source by
91 bonding them into the same molecule. This procedure was successfully applied to SiC [59] but did
92 not lead to a complete carbothermal reduction for TiC and SiC-TiC composites [60-62]. In addition,
93 this route is complex and implies a thorough control of the synthesis conditions. Another way to
94 create proximity would be to trap the carbon source in the network of a polymer material by a sol-gel
95 process, before the carbothermal reduction. This route was applied to produce TiC, ZrC-SiC and
96 TiC-SiC materials [63-65]. The co-condensation of the two alkoxide precursors leads to
97 interpenetrated networks of the two oxides with enclosed carbon source particles. The carbothermal
98 reduction produced a homogenous nanocomposite with a good repartition of both carbides and small
99 size crystallites [66-68]. Sucrose is an interesting carbon source as it is cheap and highly soluble in
100 several media, it was successfully used by several authors [33, 56, 57, 69, 70].

101

102 In this paper, we propose to associate SiC with TiC in a nanocomposite material for high temperature
103 bulk solar absorber applications. We present a synthesis route where the two metal oxide precursors

104 copolymerize, in the presence of sucrose as the carbon source, leading to an intimate mixture. In
105 order to improve the optical and mechanical properties, the resulting powders were sintered by Spark
106 Plasma Sintering (SPS) to produce materials with various densities. The samples morphology and
107 composition were characterized by several techniques including Scanning Electron Microscopy
108 (SEM), Energy-Dispersive X-Ray Spectroscopy (EDX), X-Ray Diffraction (XRD), carbon and
109 oxygen elemental analyses. The effects of the material relative density and of its surface roughness
110 on the optical properties and spectral selectivity were studied by reflectance measurements in the
111 0.25 to 25 μm wavelength range. The results were compared to those of pure SiC and pure TiC with
112 various densities.

113

114 **2. Material and methods**

115 **2.1. Semi-molecular route**

116 The objective was to create an intimate mixture of the two metal oxide precursors and the carbon
117 source during the gelling. As the precursors have a different reactivity, capping agents like
118 carboxylic acids, acetylacetone or ethylene glycol can be used to modify the surface chemistry of the
119 precursors and lower their reactivity [71-74]. The synthesis route is described on Figure 1 and
120 detailed in Supplementary Information 2. Titanium isopropoxide (TTIP) and tetraethyl orthosilicate
121 (TEOS) were chosen as the source of titanium and silicon, respectively. The system was kept under
122 inert atmosphere by nitrogen flow to prevent unintended reactions among the raw materials and
123 water. All additions were made dropwise under continuous stirring and heating at 90°C. Because
124 TTIP is much more reactive than TEOS, its reactivity was first lowered by complexation with citric
125 acid dissolved in absolute ethanol. Then, TEOS was added to the mixture, followed by sucrose
126 dissolved into water. The co-condensation was favored by the addition of sodium fluoride. The
127 solution was first concentrated under vacuum distillation and the resulting gel was freeze dried,
128 grounded and sifted to produce a homogeneous powder.

129

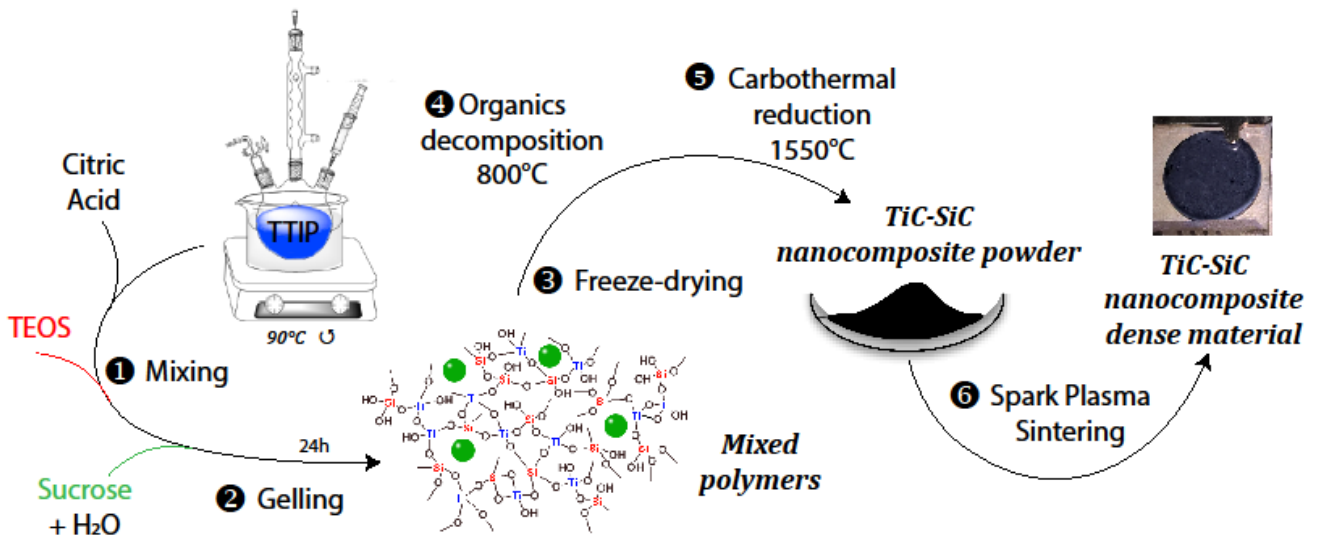


Figure 1: Reaction scheme of the synthesis route

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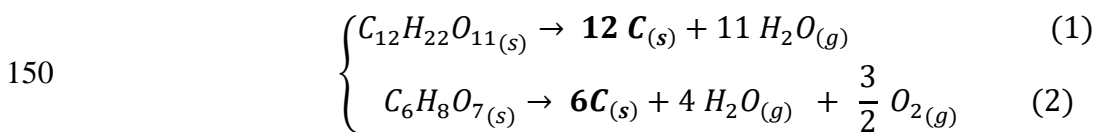
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132

133 Two heat treatments were applied under argon flow (30 L.h⁻¹); the first one at 800°C enabled to
 134 decompose the organic parts of the precursors (sucrose and citric acid) into carbon. According to
 135 Equation (1), the decomposition of one equivalent of sucrose could provide for a maximum of 12
 136 equivalents of carbon. However, according to the literature, the decomposition of sucrose leads to the
 137 formation of various carbon gaseous compounds (CH₄, C_nH_{2n}, CO₂...), leaving about 48% of
 138 efficient carbon [33]. Similarly, the decomposition of one equivalent of citric acid could provide for
 139 a maximum of 6 equivalents of carbon (Equation 2). According to several studies [75-77], after the
 140 melting of citric acid at 153°C, this compound decomposes into aconitic acid and then in citra/ita-
 141 conic anhydride by dehydration and decarboxylation reactions in the range of 160-270°C. At higher
 142 temperature, several gaseous compounds are formed and the proportion of residual carbon ranges
 143 between 5 and 45%. The amount of residual carbon depends on the processing parameters, heating
 144 rate especially, but also on the complexation of citric acid with metallic element [74]. When they are
 145 mixed with the other components of the synthesis, the behavior of sucrose and citric acid may be
 146 different than when they are heated alone. The second heat treatment at 1550°C led to the
 147 carbothermal reduction of oxides into carbides according to Equation 3.

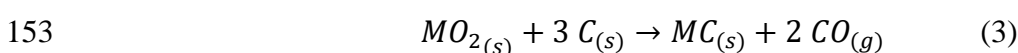
148

149 **Sucrose and citric acid decomposition - T = 800°C**



151

152 **Carbothermal reduction - T = 1550°C**



153

$$154 \quad R = \frac{12 \cdot n_{C_{12}H_{22}O_{11}}}{3 \cdot n_{MO_2}} + \frac{6 \cdot n_{C_6H_8O_7}}{3 \cdot n_{MO_2}} \quad (4) \quad F = \frac{n_{Ti}}{n_{Ti} + n_{Si}} = \frac{n_{TTIP}}{n_{TTIP} + n_{TEOS}} = 30\% \quad (5)$$

155

156 The ratio R (Equation 4) quantifies the carbon content resulting from the decomposition of sucrose
 157 and citric acid according to the Equations (1) and (2). Because the decomposition of sucrose and
 158 citric acid produces not only effective carbon but also carbon gaseous species, the amount of carbon
 159 available for the carbothermal reduction is not easily predictable and varies depending on the
 160 conditions. The value of the R ratio leading to a stoichiometric carbothermal reaction is empirical.
 161 According to preliminary studies, the R ratio was chosen to be 2.19 [60]. The F ratio defines the
 162 relative proportions of Ti and Si in the final material (Equation 5). The amounts of TEOS and TTIP
 163 used in the synthesis were adapted to produce a 30% at TiC – 70% at SiC composite, with an atomic F
 164 ratio of 30%.

165

166 **2.2. Shaping**

167 Sintering

168 To produce materials with various densities, Spark Plasma Sintering process was used on the
 169 composite powder resulting from the semi molecular route. Reference samples of pure TiC and pure
 170 SiC were also made from TiC (98%) and SiC (97.5%) powders supplied by Sigma-Aldrich with an
 171 average particle size of 3 μm and 17 μm, respectively. Sintering was conducted by Spark Plasma
 172 Sintering apparatus (Fuji-Syntex, Dr Sinter 825, Japan) under dynamic vacuum to avoid grain
 173 growth. A sufficient amount of powder was poured into a graphite die with an inner diameter of 20.4
 174 mm. A compressive graphite foil (0.2 mm thick, Papyex©, Mersen Goup, France) was used as
 175 lubricant to coat the inner surface of the die and the surface of the punches. The powder was heated
 176 under vacuum to a maximal temperature between 1300°C to 1950°C for 5 minutes with a heating
 177 rate of 200°C/min. The heating rate was decreased at 50°C/min the last minute of heating, to avoid
 178 an overshoot. A uniaxial pressure of 75 MPa was applied upon heating. Cooling rate was
 179 100°C/min. SPS is commonly used to sinter Ultra High Temperature Ceramics [78, 79].

180

181 Polishing

182 To produce mirror polished surfaces, the densified materials were polished with a Beta Buehler
 183 grinder-polisher, with SiC grinding papers and with 1 μm diamond paste (Struers) according to the
 184 procedure described in Table 1. To study the effects of surface roughness on the optical properties,
 185 the surface of several samples was scratched with SiC grinding papers with increasing grain size, the
 186 results of this preliminary study are given in Supplementary Information 1.

Polishing step	Grinding SiC paper		Rotation speed (rpm)	Time (min)
	Grit (grain/cm ²)	Grain size (μm)		
1	1200	15.3	200	2
2	2000	10.3	200	5
3	4000	5	200	5 - 10
4	Diamond	1	200	15 - 20

Table 1: Polishing procedure.

187

188

189 2.3. Characterization methods

190 Optical properties

191 Two spectrophotometers were used to measure the total spectral reflectance of the samples. Over the
 192 wavelength range from 0.25 to 2.5 μm, the near-normal hemispherical ($R^{\perp,\circ}$) reflection spectrum
 193 was acquired with a 10 nm step using a Perkin Elmer Lambda 950 spectrophotometer. This apparatus
 194 was equipped with deuterium and tungsten lamps, PMT and InGaAs detectors, and a 150 mm
 195 integrating sphere coated with Spectralon diffuse reflective coating. The sample was illuminated at
 196 an incidence angle of 8°.

197 Over the wavelength range from 1.25 μm to 25 μm, the hemispherical directional reflectance ($R^{\circ,\theta}$)
 198 was recorded at different detection angles θ from 8 to 80°, using a SOC-100 HDR reflectometer
 199 (Surface Optics Corporation) coupled with a Nicolet (Fourier Transform InfraRed spectroscopy)
 200 FTIR 6700 spectrophotometer. A gold coated calibrated specular reflectance standard was used as
 201 reference during measurements (NIST calibration). The spectral range from 1.25 to 25 μm was
 202 covered by a FTIR equipped with InGaAs and DTGS/KBr detectors, coupled with Quartz and KBr
 203 beamsplitters, respectively. The sample was illuminated from all directions using a 700°C (973 K)
 204 blackbody as the infrared source and a 2π imaging gold coated hemi ellipsoid. The light reflected by
 205 the sample at a chosen detection angle was collected by a moveable overhead mirror which directed
 206 the collimated beam into the FTIR apparatus for signal treatment to retrieve the reflectance spectrum.
 207 Each reflectance spectrum was derived from 64 consecutive scans on the same sample.

208 The total spectral reflectance measured and the solar spectrum were interpolated over the wavelength
 209 range from 0.25 to 25 μm with a step of 2 nm to calculate the optical parameters, using Mathematica
 210 software. The solar absorptance α was calculated from room temperature measurements in the
 211 wavelength range 0.25 to 4 μm, according to Equation 6. The near-normal thermal emittance $\varepsilon_{\mathcal{S}}(T_a)$
 212 and the hemispherical emittance $\varepsilon_H(T_a)$ at room temperature were calculated in the wavelength
 213 range 1.25 to 25 μm according to Equations 7 and 8 respectively. The hemispherical emittance
 214 represents the propensity of a surface illuminated from all directions of the hemisphere surrounding

215 it to reemit radiation in the same hemisphere. As reported in the results section, at room temperature
 216 and for this type of samples, the emittance calculated from near-normal reflectance measurement is
 217 representative of the hemispherical emittance. Spectral transmittance was not measured, as the
 218 samples were opaque over the whole considered spectral range.

219

$$220 \quad \alpha = \frac{\int_{0.25 \mu\text{m}}^{4 \mu\text{m}} [1 - R_{8^\circ}(\lambda, T_a)] \cdot G(\lambda) \cdot d\lambda}{\int_{0.25 \mu\text{m}}^{4 \mu\text{m}} G(\lambda) \cdot d\lambda} \quad (6) \quad \varepsilon_\theta(\theta, T_a) = \frac{\int_{1.25 \mu\text{m}}^{25 \mu\text{m}} [1 - R(\lambda, T_a, \theta)] \cdot P(\lambda, T_a) \cdot d\lambda}{\int_{0.25 \mu\text{m}}^{25 \mu\text{m}} P(\lambda, T_a) \cdot d\lambda} \quad (7)$$

$$221 \quad \varepsilon_H(T_a) = 2 \int_0^{\pi/2} \varepsilon_\theta(\theta, T_a) \cdot \sin \theta \cdot \cos \theta \cdot d\theta \quad (8)$$

222 With λ : the wavelength [μm], $R_{8^\circ}(\lambda, T_a)$ and $R(\lambda, T_a, \theta)$: the spectral reflectance of the sample
 223 measured at room temperature (T_a) with an illumination angle of 8° or with a variable detection angle
 224 θ , $G(\lambda)$: the standard solar irradiance spectrum (ASTM-G173 AM1.5 direct + circumsolar) [$\text{W}\cdot\text{m}^{-2}\cdot\mu\text{m}$],
 225 $P(\lambda, T_a)$: spectral emittance (exitance) of a blackbody at room temperature derived from
 226 Planck's law [$\text{W}\cdot\text{m}^{-2}\cdot\mu\text{m}$].

227 Porosity, density and roughness

228 The apparent density (ρ_{app}) of the sintered samples was measured by hydrostatic weighting in pure
 229 water, using Archimedes method. Helium pycnometry measurements were conducted to determine
 230 the pycnometric density (ρ_{pycno}). The theoretical density (ρ_{th}) of the mixed carbide materials was
 231 calculated using a rule of mixtures taking into account the Si/Ti measured proportions and the
 232 amounts of free C and O. These densities were used to determine the relative density (D), the open
 233 and closed porosities (ϕ_{open} and ϕ_{closed}) according to the equations reported in Supplementary
 234 Information 3.

235 The surface roughness of the materials was measured by means of optical interferometry (Fogale
 236 Nanotech – Microsurf 3D). This apparatus gives the global roughness of a $287 \mu\text{m} \times 481 \mu\text{m}$ area.
 237 For each sample, a least six areas were measured to obtain an average roughness value.

238 Morphology, composition and structure

239 The morphology of the samples was studied by Scanning Electron Microscopy (SEM), with an FEI
 240 Quanta 200 ESEM equipped with a Field Emission Gun. SEM images were recorded with back-
 241 scattered electrons (BSE) for composite samples and with secondary electrons (SE) for pure TiC and
 242 SiC samples. Energy Dispersive Spectra (EDX) were recorded using a Bruker SDD 5030 detector
 243 with a 123 eV resolution at the Mn ($K\alpha$) line. EDX was used to verify the composition of the
 244 synthesized products and to study the effects of oxidation.

245 The global Ti/Si proportion was also measured by X-Ray Fluorescence (XRF), using a Spectro-
 246 Xepos apparatus with four secondary targets (Mo, Al_2O_3 , Co and HOPG Bragg crystal).

247 Carbon and Oxygen analyzers (LECO CS230 and ON736) were used to measure the total carbon and
 248 oxygen contents, respectively. The samples were heated under an oxygen flow for carbon analysis or
 249 in a graphite environment for oxygen analysis. In both cases, the formation of carbon oxides was
 250 detected and quantified by infrared spectroscopy, then related to the total carbon or oxygen content
 251 in the samples. Added Fe powder was used to assist the combustion in the case of carbon analysis.

252

253 The samples were characterized by X-Ray Diffraction (XRD) using the Bruker D8 advance
 254 diffractometer equipped with lynxeye detector and using Cu K α radiation ($\lambda=1.54184\text{\AA}$). Data were
 255 acquired in reflection geometry (parallel beam) in the 10-110° (2 θ) or 10-90° (2 θ) range of angles
 256 with steps of 0.019°. Silicon powder was collected and used as standard to evaluate the instrumental
 257 function. All the collected XRD patterns were refined by the Rietveld method with the use of the
 258 Fullprof suite package [80, 81]. TiC compound was found to crystallize in the cubic NaCl structure
 259 type in the Fm-3m space group, whereas SiC crystallizes in the ZnS structure type in the F-43m
 260 space group. During the refinement, several profile/structure parameters were allowed to vary such
 261 as zero shift, scale factor, isotropic thermal factor, unit cell parameters, moreover an anisotropic size
 262 model was applied in order to evaluate the microstructural effect. An example of the results of the
 263 Rietveld refinement obtained for the TiC compound with a relative density of 78 % is available in
 264 Supplementary Information 4.

265

266 3. Results

267 3.1. Characterization of the final products

268 All the results concerning the composition and the physical shape of the samples are reported in
 269 Table 2.

Sample	Processing parameters	Composition			Sintered materials characteristics			
	T sintering (°C)	Ti/Si proportion (%mol)	C (%mass)	O (%mass)	Relative density (%)	Open porosity (%)	Closed porosity (%)	Surface roughness (nm)
TS-57	1450	31 / 69	26.6	7.2	56.6	43.4	0	52
TS-82	1550	32 / 68	25.3	5.5	81.6	16.7	1.8	20
TS-92	1650	31 / 69	26.2	6.0	92.3	6.3	1.4	13
TS-96	1750	32 / 68	26.0	5.0	95.8	1.2	3.1	10
TiC-78	1300	100 / 0	20.0	0.67	77.9	19.1	3.0	38
TiC-91	1400	100 / 0	20.7	0.56	90.5	6.9	2.6	11
TiC-94	1500	100 / 0	19.5	0.54	94.4	2.7	2.9	17
TiC-96	1700	100 / 0	19.6	0.47	95.8	1.5	2.8	15
TiC-97	1850	100 / 0	19.6	0.46	96.6	1.1	2.4	6
SiC-72	1950	0 / 100	30.4	0.20	72.1	26.5	1.4	24

270 *Table 2: Composition and measured characteristics of materials after SPS sintering for 5 min at $P = 75\text{MPa}$ at the*
271 *sintering temperature indicated in the table. Ti/Si proportion was obtained by average between XRF and SEM-EDX*
272 *analyses. The theoretical %mass of C is 26 %, 20 % and 30 %, for TS composites, pure TiC and pure SiC samples,*
273 *respectively. The error is about 0.1% for elemental analyses, relative density, and open and closed porosity. The error is*
274 *about 1 nm for surface roughness and about 1%at for Ti/Si proportion.*

275

276 The XRF and EDX analyses reported on Supplementary Information 5 indicate a Ti / Si proportion,
277 respectively higher and lower than the theoretical values. Nevertheless, the average values (Table 2)
278 are close to the theoretical ones, the synthesized composites have the expected Ti / Si proportion.
279 The amount of C globally decreases with the increase in the sintering temperature. The amount of C
280 is close to the theoretical value (27 %, 20 % and 30 %, for TS composites, pure TiC and pure SiC
281 samples, respectively) and the O content is higher for the composite than for the pure TiC and SiC.
282 This high O content could be due to a insufficient amount of C available for the carboreduction after
283 the sucrose decomposition at 800°C . Another explanation could be a too low temperature for the
284 carboreduction, as the O content tends to decrease when the sintering temperature increases.

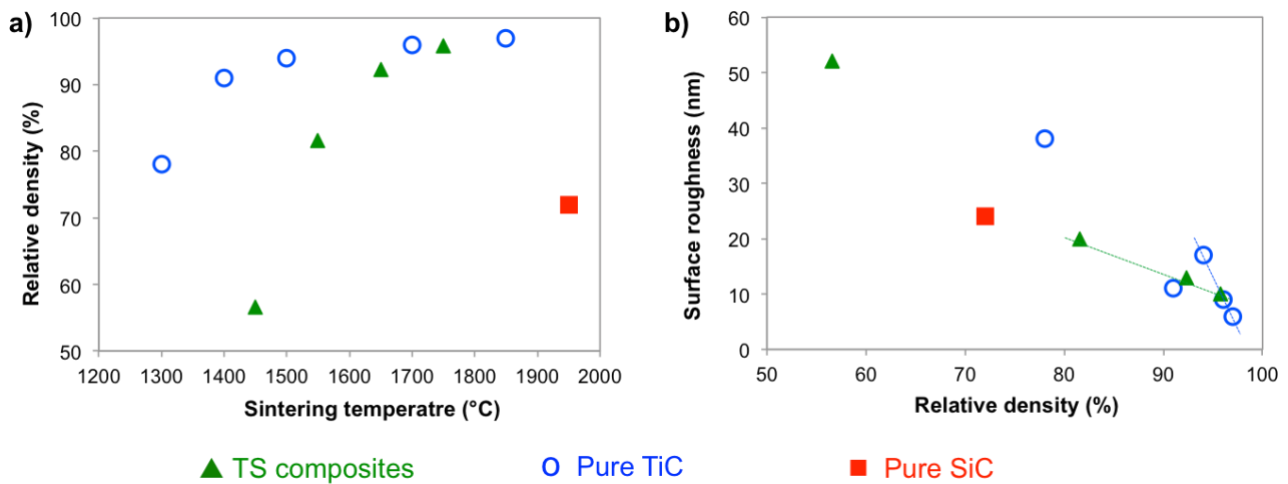
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286 As expected, the relative density of the materials increases with the sintering temperature (Figure 2-
287 a) [43, 82-84]. For the pure SiC sample, full relative density could not be achieved, even with a
288 sintering temperature of 1950°C . SiC is known to be difficult to sinter because of its highly covalent
289 bonded characteristic and the resulting low self-diffusion coefficient [85, 86].

290 For all samples, the open porosity decreases when increasing the sintering temperature and thereby
291 with the relative density (Table 2). In the case of the composite samples, the closed porosity
292 increases with the sintering temperature and thereby with the relative density, while it remains
293 constant in the case of TiC samples (Table 2). During the sintering some of the open pores are
294 closed, leading to an increase of the closed porosity.

295 The relative density of all samples appear to be correlated with the surface roughness (Figure 2-b).
296 The evolutions are almost linear for the denser materials with the exception of sample TiC-91 which
297 shows a surprisingly low value of surface roughness (11 nm). The slope of the curve is much higher
298 for TS composites than for the pure TiC samples, meaning that the decrease in the relative density
299 induces a stronger increase in surface roughness for pure TiC samples. The open porosity consists in
300 surface holes which are partly taken into account in the value of the surface roughness.

301



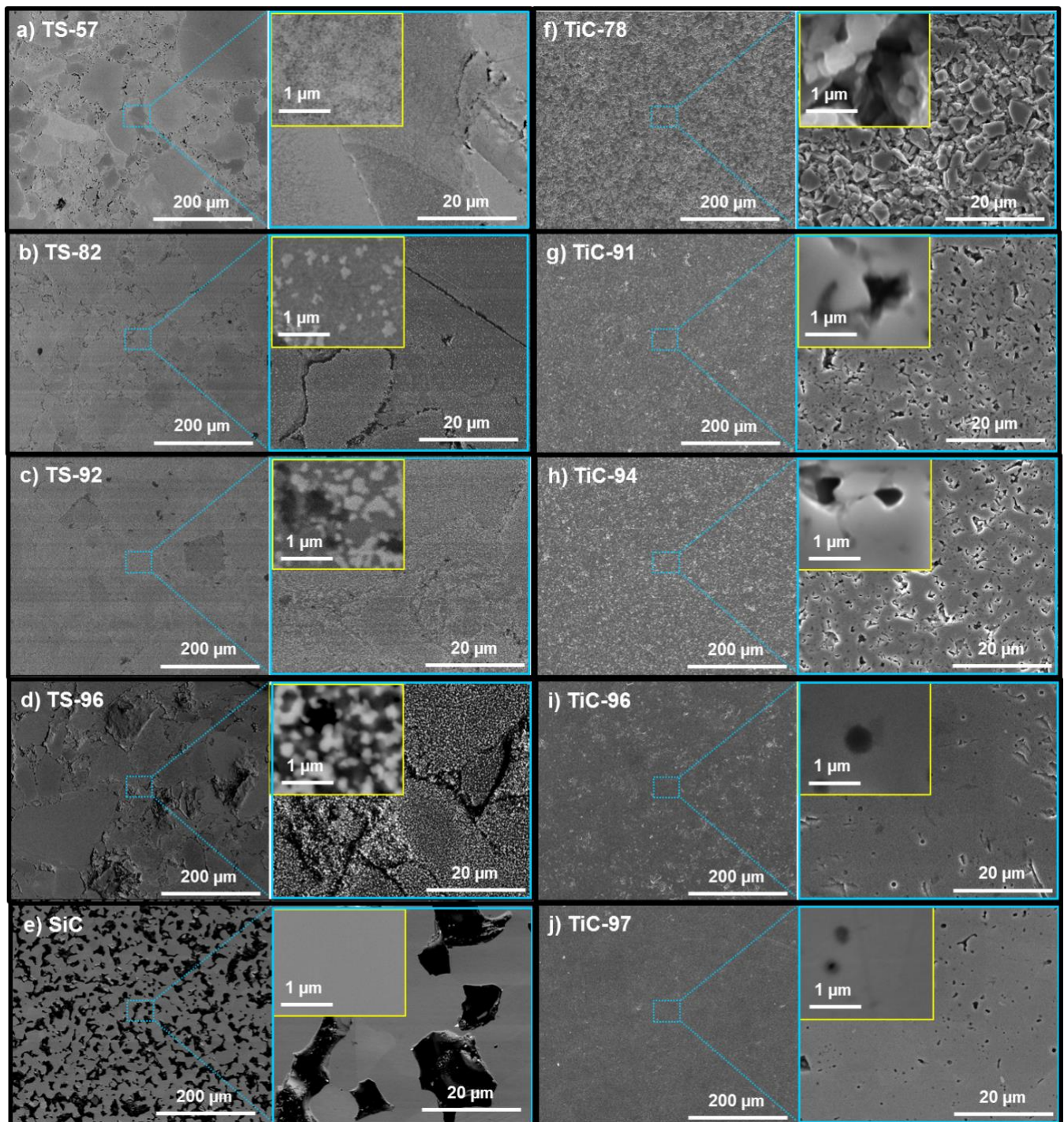
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303 Figure 2: a) Evolution of the relative density as a function of the sintering temperature and b) evolution of the surface
 304 roughness as a function of the relative density. The dashed lines in b) are a guide for the eyes.

305

306 The morphology of the sintered materials was characterized by SEM to study the TiC and SiC grains
 307 size and distribution (Figure 3). All composites present large areas with various electronic contrasts
 308 due to changes in porosity and/or in composition. With the exception of sample TS-57, the electronic
 309 contrast between the TiC grains (white) and the SiC matrix (gray) is marked (Figure 3-b to d). The
 310 repartition of TiC grains within the SiC matrix is globally homogeneous at a short range while
 311 presenting slight variations from one area to another. The presence of open porosity is confirmed by
 312 SEM observation. The pore size is about 1 μm or lower for most samples, and several microns for
 313 the samples with the lowest densities (SiC, TS-57, TiC-78). In TS-57, it is not possible to distinguish
 314 TiC from SiC grains, the morphology of the sample surface looks like those of non sintered powders
 315 (see Supplementary Information 6) which could be due to the low relative density of the sample. In
 316 all composites excepted TS-57, the TiC grains have the same size (about 150 nm). However, when
 317 increasing the sintering temperature and thereby the relative density of the sample, the TiC grains are
 318 brought closer, forming bigger white zones with less overall porosity.

319 In the case of the pure SiC sample (Figure 3-e), the grains are much bigger (about 17 μm) and the
 320 open porosity is obvious. In the case of the TiC samples, the grains are smaller (about 3 μm) and the
 321 decrease in open porosity is also visible in the SEM images (Figure 3-f to j).



322
 323 Figure 3: SEM images of the surface of the composite samples in BSE mode to show the Ti/Si distribution (a-d), the SiC
 324 reference (e) and the TiC samples (f-j) in SE mode to show the topography since there is a unique carbide phase.

325

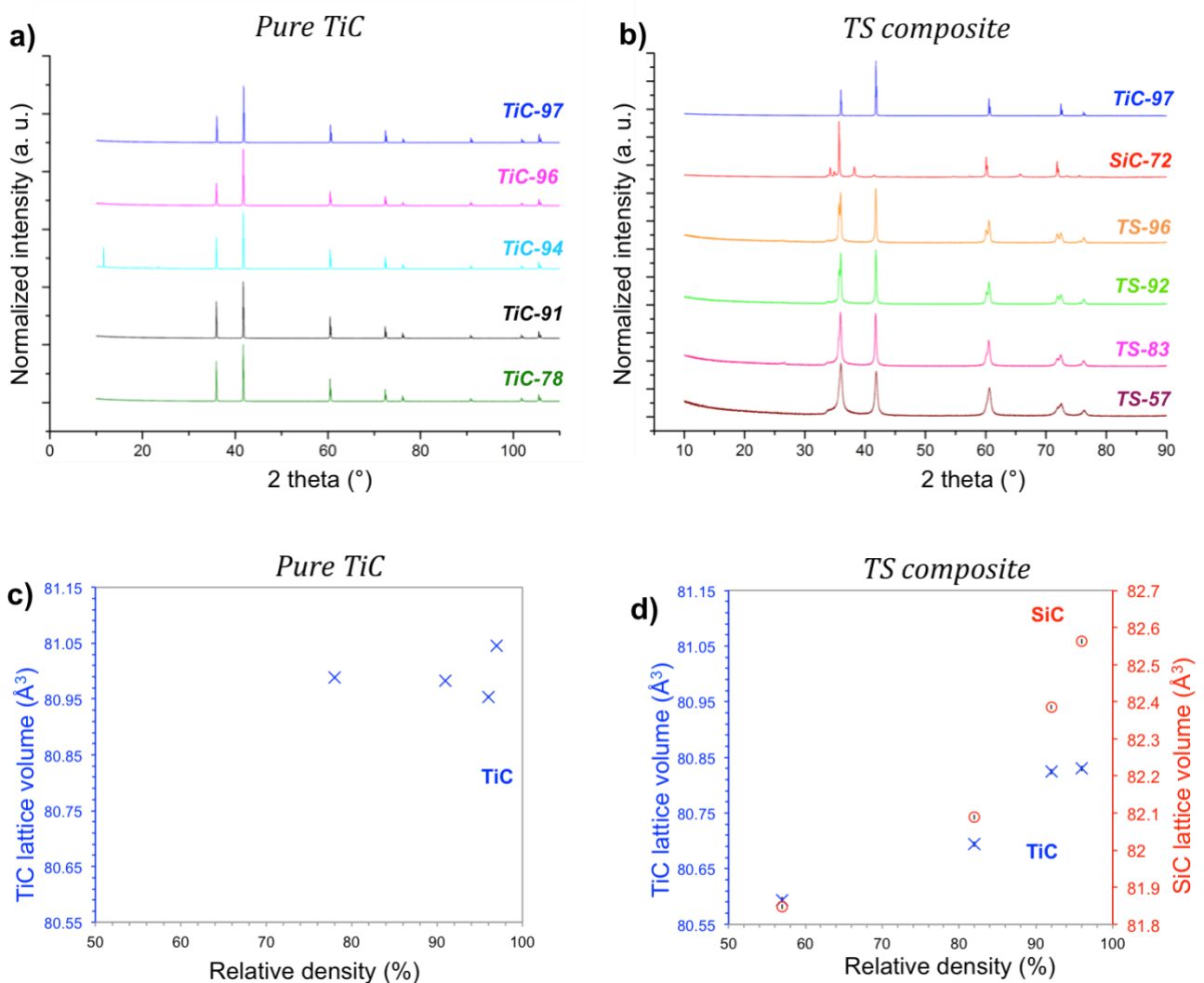
326 After sintering, the samples were also analyzed by PXRD (Figure 4-a, b) and the results of the
 327 Rietveld refinement are presented in Figure 4-c, d) and in Table 3.

328 In the case of pure TiC samples, almost all the collected data showed the formation of pure and
 329 single phase. In the case of sample TiC-94, there is a reflexion around $2\theta = 10^\circ$ which makes the
 330 Rietveld refinement impossible. From the data reported in Table 3; the obtained TiC compounds are
 331 almost free from O contamination and the O content decreases with the increase in the sintering

332 temperature. These results are in good agreement with the values determined by O elemental
 333 analysis. The lattice volume of TiC is similar whatever the sample relative density and consistent
 334 with the bibliography (Figure 4-c) [87]. Unfortunately, in the pure SiC sample sintered from the
 335 commercial powder, the SiC phase crystallizes in the hexagonal system in several polymorphs which
 336 making the Rietveld refinement impossible.

337

338 In the case of the SiC-TiC composites, both TiC and SiC cubic phases are present (Figure 4-b).
 339 However, the possible incorporation of low amounts of Si in the TiC cubic structure (Ti or C sites)
 340 [88] makes the Rietveld refinement complex to interpret and it was not possible to calculate precisely
 341 the O content. The TiC and SiC unit cell parameters increase with the sintering temperature and
 342 therefore with the sample relative density (Figure 4-d). One explanation could be the elimination of
 343 the residual oxygen within the structure of both TiC and SiC phases as the sintering temperature
 344 increases.



345

346 *Figure 4: a, b) X-ray diffractograms of all the samples of this study and c, d) evolution of the TiC and SiC volume*
 347 *parameters as a function of the sample density. In c) and d), the error is about 10⁻³ Å³.*

348

Sample	T sintering (°C)	Relative density (%)	O (%wt) elemental analysis	O (%wt) XRD	TiC lattice volume (Å ³)	SiC lattice volume (Å ³)
TS-57	1450	56.6	7.2	-	80.594	81.848
TS-82	1550	81.6	5.5	-	80.694	82.088
TS-92	1650	92.3	6.0	-	80.824	82.386
TS-96	1750	95.8	5.0	-	80.83	82.562
TiC-78	1300	77.9	0.67	0.69	80.988	-
TiC-91	1400	90.5	0.56	0.54	80.983	-
TiC-94	1500	94.4	0.54	-	-	-
TiC-96	1700	95.8	0.47	0.51	80.954	-
TiC-97	1850	96.6	0.46	0.15	81.045	-
SiC-72	1950	72.1	0.20	-	-	-

349 Table 3 : Data obtained by Rietveld refinement from PXRD measurements: TiC and SiC lattice volumes and O %wt.

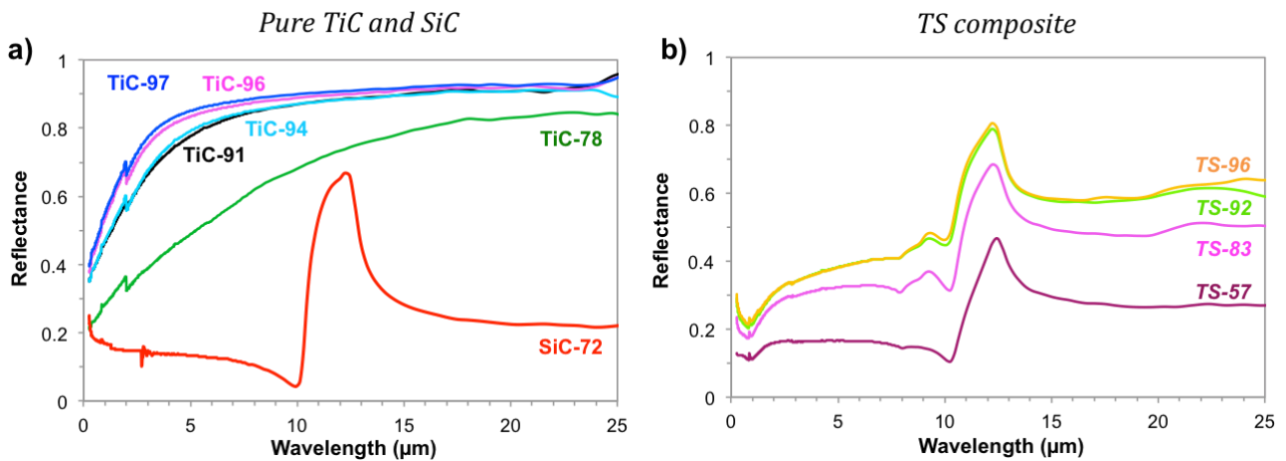
350 Comparison with the O %wt measured by elemental analysis.

351

352 3.2. Optical properties

353 To evaluate the optical properties of the samples, the total spectral reflectance was measured in the
354 0.25 to 25 μm wavelength range with a near normal detection (8°) (Figure 5). It appears that the
355 reflectance of the pure TiC samples increases with the relative density, in the whole wavelength
356 range. The effect is small between the samples with close densities (TiC-97 to TiC-91) and more
357 marked with the less dense sample TiC-78. The reflectance of SiC is much lower than those of TiC
358 samples and displays the characteristic peak in the 10-14 μm range. In the case of the TS composite,
359 the reflectance curves are located between those of pure TiC and pure SiC and also display the SiC
360 characteristic peak. The reflectance increases with the relative density of the sintered TS composite
361 and the curves of the samples sintered at 1650°C and 1750°C (TS92 and TS96) are almost
362 superimposed.

363



364

365 Figure 5: Evolution of the total near normal spectral reflectance for a) the pure TiC and SiC, and b) the TS composites.

366

367 4. Discussion

368

369 These materials are sought for constituting the absorber in concentrating solar power devices. In this
370 context, they must fulfil several characteristics including good optical properties and good oxidation
371 resistance. From the results presented above, the effects of the relative density and of the surface
372 roughness on the optical properties are discussed below. However, the effects on the oxidation
373 resistance were not studied here. Coulibaly et al. showed that TiC-SiC composite materials have a
374 better oxidation resistance than pure TiC [33] and on-going work should bring new information
375 about this topic.

376

377 *Effects of the sintering temperature on the material relative density, composition and structure*

378 The TiC samples on one hand, and the composite samples on the other hand, were sintered from the
379 same powders (commercial product and synthesised by semi-molecular route, respectively) at a
380 temperature ranging from 1300 to 1850°C. As presented in Table 2 and Figure 2, the relative density
381 of the final material increased with the increase in the sintering temperature. Sintering did not
382 induced the emergence of secondary phases, at least not in a sufficient amount to be detected by
383 XRD (Figure 4). In the case of the composite, the sintering process did not modify the overall Si-Ti
384 proportion (Table 2) or induce TiC grain growth. However, it favored their aggregation (in denser
385 samples, TiC grains distribution is less homogeneous) (Figure 3). In addition, the increase in
386 sintering temperature lowered the total O content in the final material which increased the volume of
387 the TiC lattice towards the one obtained for the pure TiC samples. This increase in volume is
388 consistent with the higher atomic radius of C compared to O. This result is in agreement with several
389 studies about the evolution of lattice parameter of $TiC_xO_{(1-x)}$ oxycarbide materials as a function of the
390 composition [87, 89].

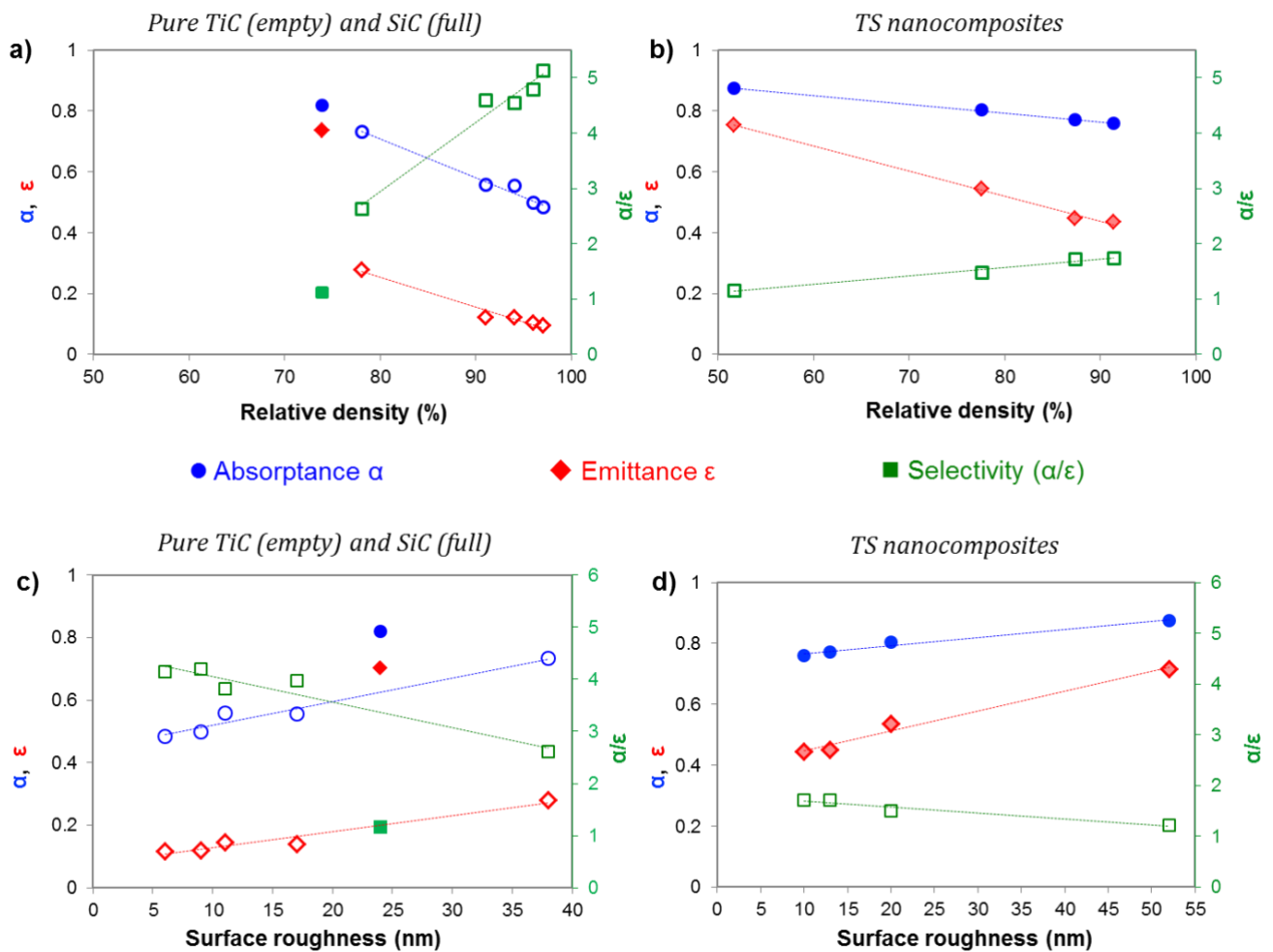
391

392 *Effects of the the material relative density on the optical properties*

393 For both series of samples, the reflectance increases with the increase in the relative density in the
394 whole range of analyzed wavelengths (Figure 5). From the near-normal spectral reflectance curves,
395 the sample total solar absorptance (α), the sample total directional and hemispherical thermal
396 emittances (ϵ_{8° and ϵ_H) have been calculated using equations (6), (7) and (8) respectively. The results
397 are reported as a function of the sample relative density on Figure 6. As expected, the increase in the
398 reflectance induces a decrease in both the absorptance and the emittance.

399 The values of hemispherical emittance calculated from multi-angle data (Equation 8) were almost the
400 same as the values of directional emittance calculated from single near-normal reflectance curve
401 (Equation 7), especially for SiC and the composite materials. The comparison is reported in

402 Supplementary Information 7. Therefore it can be remembered for further studies that at room
 403 temperature and for this type of samples, the emittance calculated from near-normal reflectance
 404 measurement is quite representative of the hemispherical emittance.
 405



406
 407 Figure 6: Evolution of the absorptance (α), the emittance (ϵ) and the selectivity (α/ϵ) as a function of (a, b) the relative
 408 density and (c, d) the surface roughness of (a, c) the pure TiC and SiC samples and (b, d) the composite samples.
 409

410 For all samples, the selectivity (absorptance / emittance) increases with the sample relative density
 411 (Figure 6-a, b) and decreases with the increase in surface roughness (Figure 6-c, d). These results are
 412 consistent with those of the literature and with those of our preliminary study reported in
 413 Supplementary Information 1 [19, 20, 23, 45-47]. For TS composites, the evolution of the optical
 414 properties as a function of the relative density or of the surface roughness are almost linear. The
 415 selectivity of samples TS-92 and TS-96 is the same. The increase in absorptance with surface
 416 roughness can be explained by the multi-reflexions effect: light is trapped by the walls of the surface
 417 holes and scratches. Light is reflected several times, increasing the absorptance [5, 6, 90]. The
 418 increase in emittance is related to the increase in specific surface area as the surface roughness
 419 increases. By definition, the quantity of energy emitted by a material is proportional to its surface.

420 When comparing with the pure SiC and pure TiC references (Figure 6-a), it appears that all
421 nanocomposite samples (Figure 6-b) have a higher selectivity than the pure SiC reference but lower
422 than the one of the pure TiC reference. Due to their good spectral selectivity, these nanocomposite
423 materials could therefore be good candidates for bulk solar applications, especially the denser ones.
424 As TS-92 and TS-96 samples have the same value of spectral selectivity, we could consider that a
425 SPS sintering temperature of 1650°C is sufficient to obtain a composite with interesting optical
426 properties.

427

428 One can wonder if the effect of the sample relative density on its optical properties is only a surface
429 effect or if the bulk has to be considered. There is a tight link between relative density and surface
430 roughness, especially for the composite samples (Figure 2-c-d).

431 In the case of the composite, the two denser samples (TS-92 and TS-96) have the same spectral
432 selectivity, their reflectance curves are almost superimposed despite a difference in relative density
433 of 4 % and a difference in surface roughness of 3 nm. In the case of the three denser TiC samples
434 (TiC-94, TiC-96, TiC-97), the difference in relative density is similar (3 %) but the difference in
435 surface roughness is much higher (7 nm), as well as the effects on the optical properties. Therefore,
436 the effects on the optical properties seems to be mainly due to changes in surface roughness, at least
437 for samples with a relative density higher than 90 %.

438

439 To thoroughly determine whether the closed porosity has an impact on the optical properties, the
440 emittance should be measured directly from the non-illuminated face of the samples and not
441 calculated from the surface reflectance curve [11]. On going work should bring new information
442 about this question.

443 The key to increase the spectral selectivity is to increase the absorptance without increasing the
444 emittance. Several ideas have been proposed in the literature, among them, the concept of directional
445 selectivity. As the incident solar radiation is directional while the radiative losses are hemispherical,
446 an optical cavity can be used to trap the incident solar radiation and reflect the emitted radiation back
447 to the absorber [91]. Similarly, Hollands et al. proposed to use corrugated specular surfaces to
448 selectively absorb the directional solar radiation while limiting the hemispherical radiation losses
449 [50]. It could also be interesting to extend the study to higher frequencies, and monitor the properties
450 of the SiC-TiC composites as electromagnetic wave absorber as it has been done for SiC/Si₃N
451 composites [92, 93].

452

453

454

455 **Conclusion**

456 In this paper the potential of SiC-TiC nanocomposite materials for bulk solar absorber applications
457 was studied. 70%at SiC – 30%at TiC nanocomposite materials were successfully synthesized by a
458 sol-gel route from alkoxides as metal oxide precursors and sucrose as the carbon source. The
459 carbothermal reduction was conducted at relatively low temperature (1550°C) compared to the
460 conventional process. The resulting powder was composed of nanometric TiC and SiC particles
461 homogeneously mixed, with 5-7 %wt of residual O. The sintering process was then adapted to
462 produce compacts with various densities. Reference materials of pure TiC with increasing densities
463 were also sintered from commercial TiC powder.

464 The spectral reflectance was measured in the 0.25 to 25 μm wavelength range to evaluate the spectral
465 selectivity of these materials. The effects of the sample relative density and surface roughness were
466 studied and their correlation was discussed. A tight link between the sample relative density and its
467 surface roughness was identified and explained by considering the open porosity as the main
468 contribution to surface roughness. The reflectance was found to increase in the whole wavelength
469 range, with the increase in relative density and the decrease in surface roughness. Therefore, the
470 denser and smoother the sample, the higher its spectral selectivity. The TiC-SiC composite had an
471 intermediate reflectance compared to the pure SiC and the pure TiC samples. With an absorptance of
472 0.76, an emittance of 0.44 and a selectivity of 1.74, the denser SiC-TiC could be a good candidate for
473 bulk solar applications. Even though these values are slightly lower than those obtained for other
474 materials like ZrB_2 , HfC or TaC, it should be recalled that these materials also have to be resistant to
475 oxidation which is the case of our SiC-TiC composite [21, 33, 94]. In addition, several solutions
476 from the literature were proposed to improve these optical properties by increasing the absorptance
477 while maintaining a low emittance.

478

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487

488 **Declarations of interest**

489 The authors declare no competing interests.

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